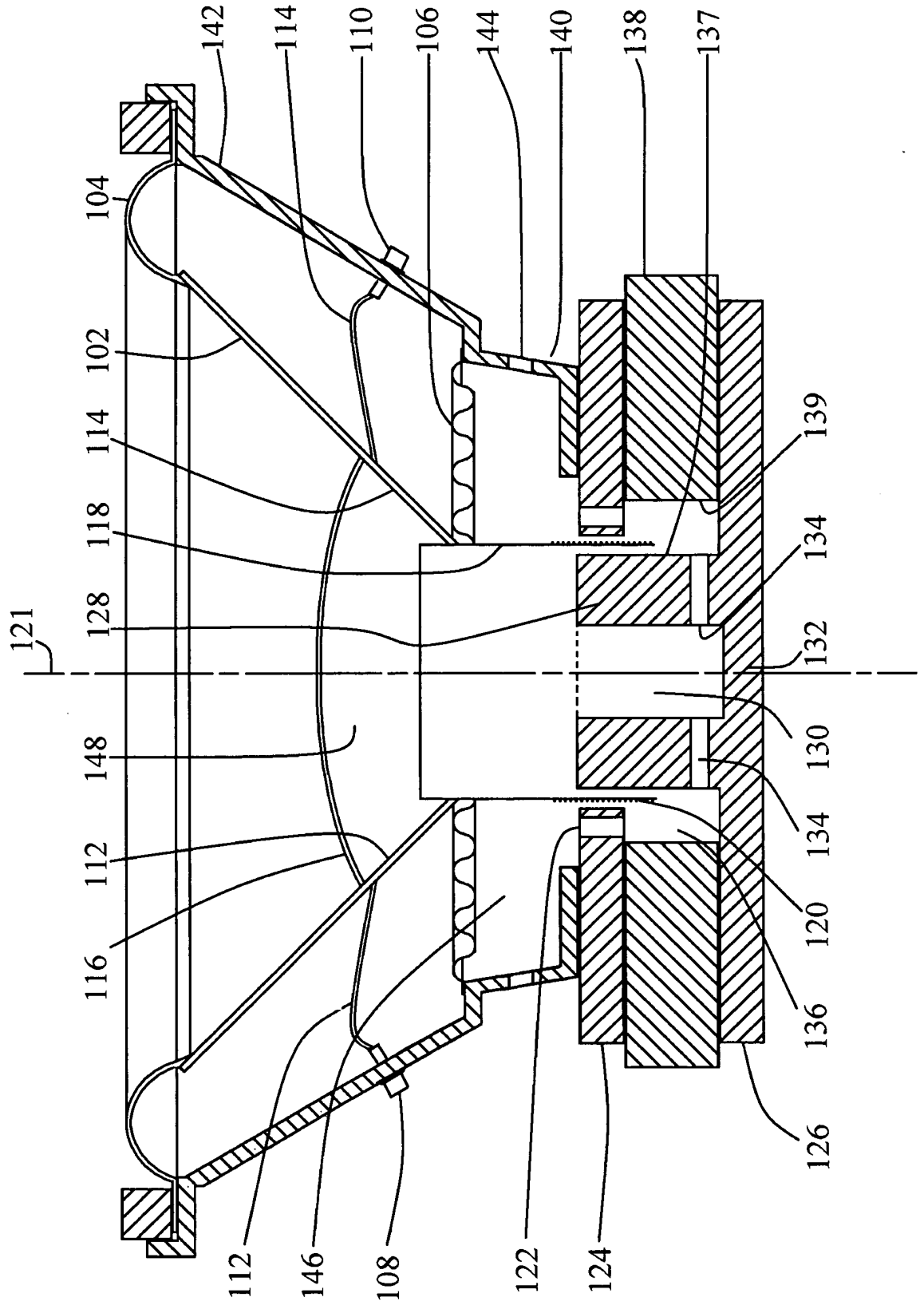




100

Figure 2



149

Figure 4a

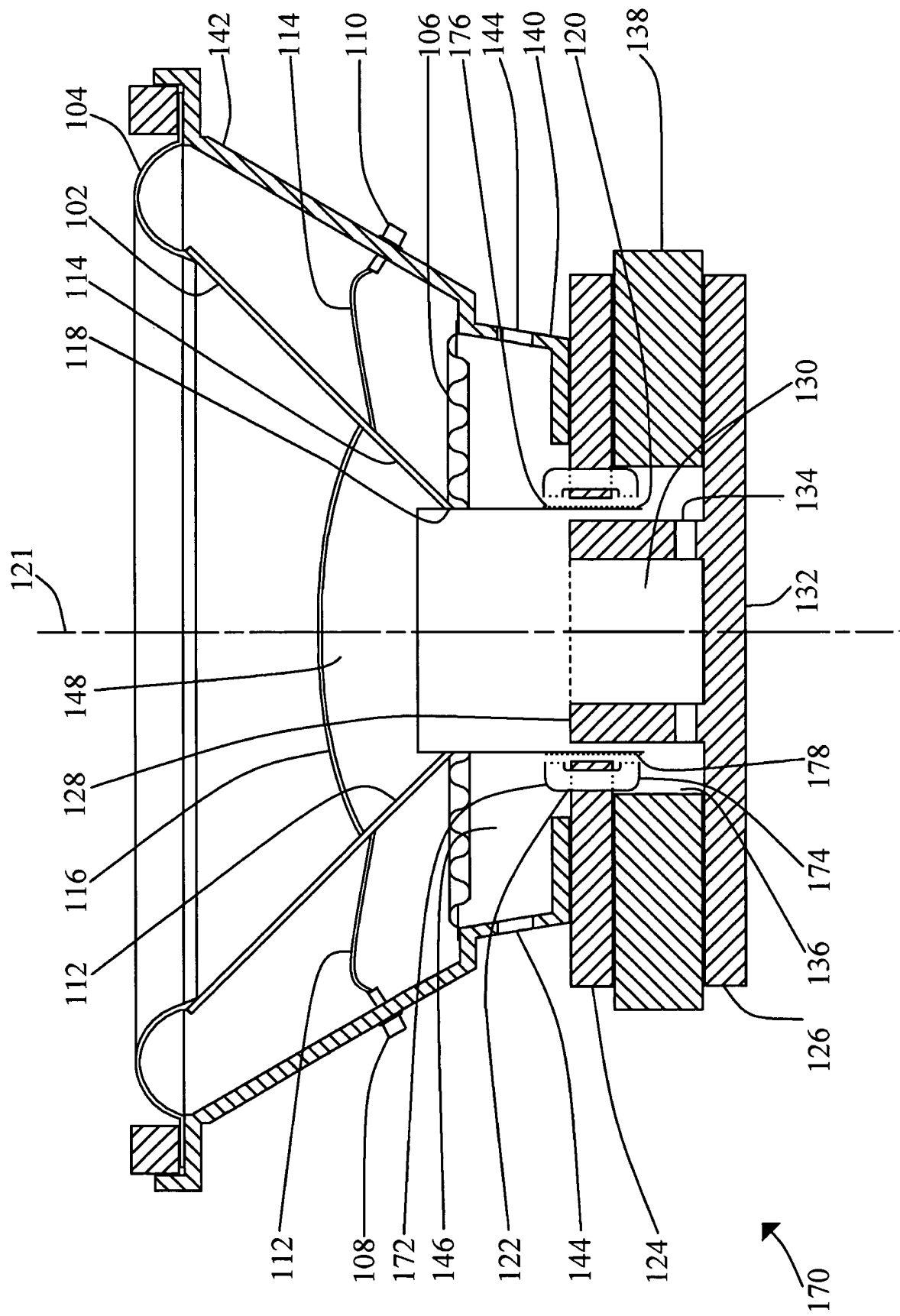


Figure 4b

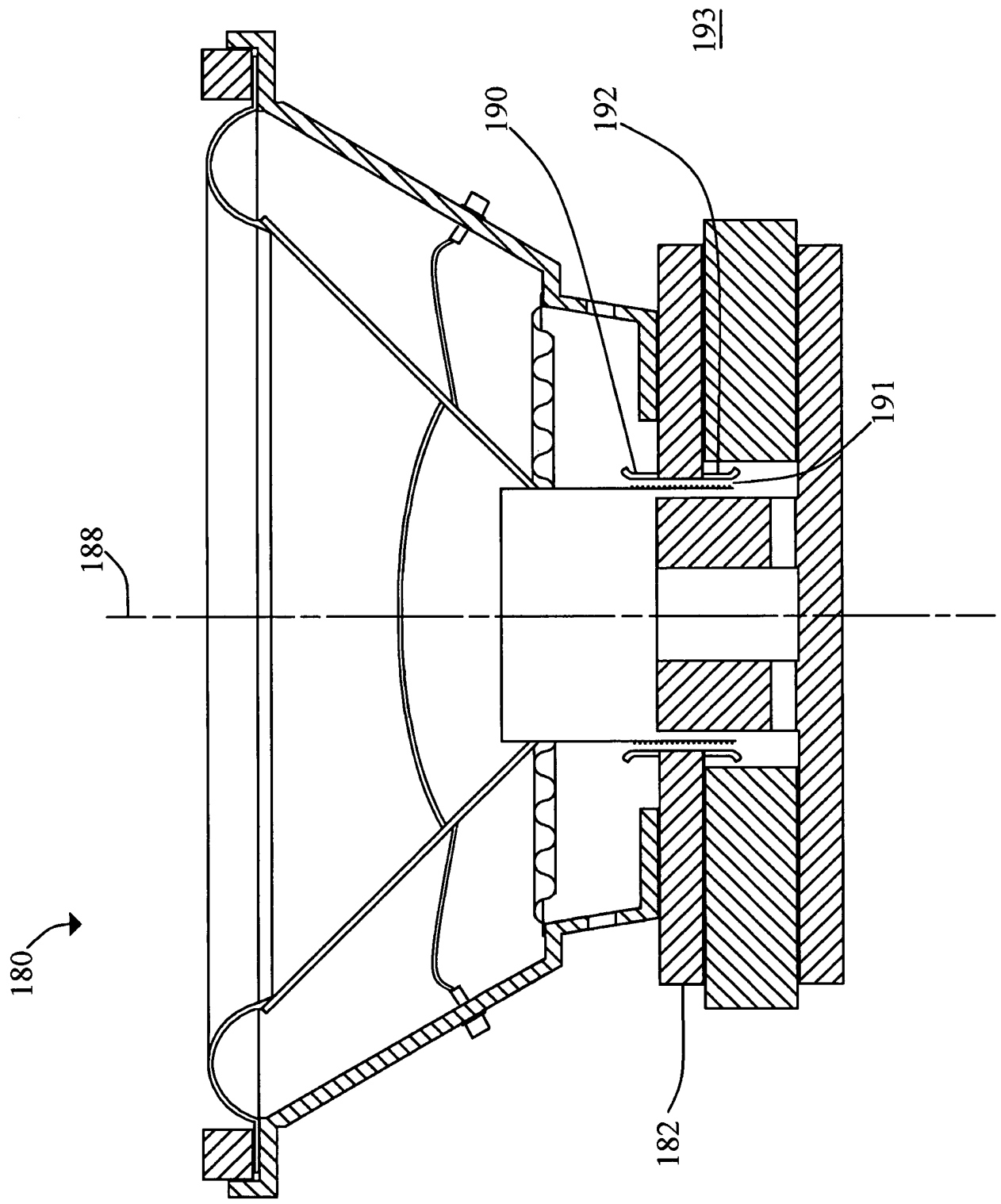


Figure 4c

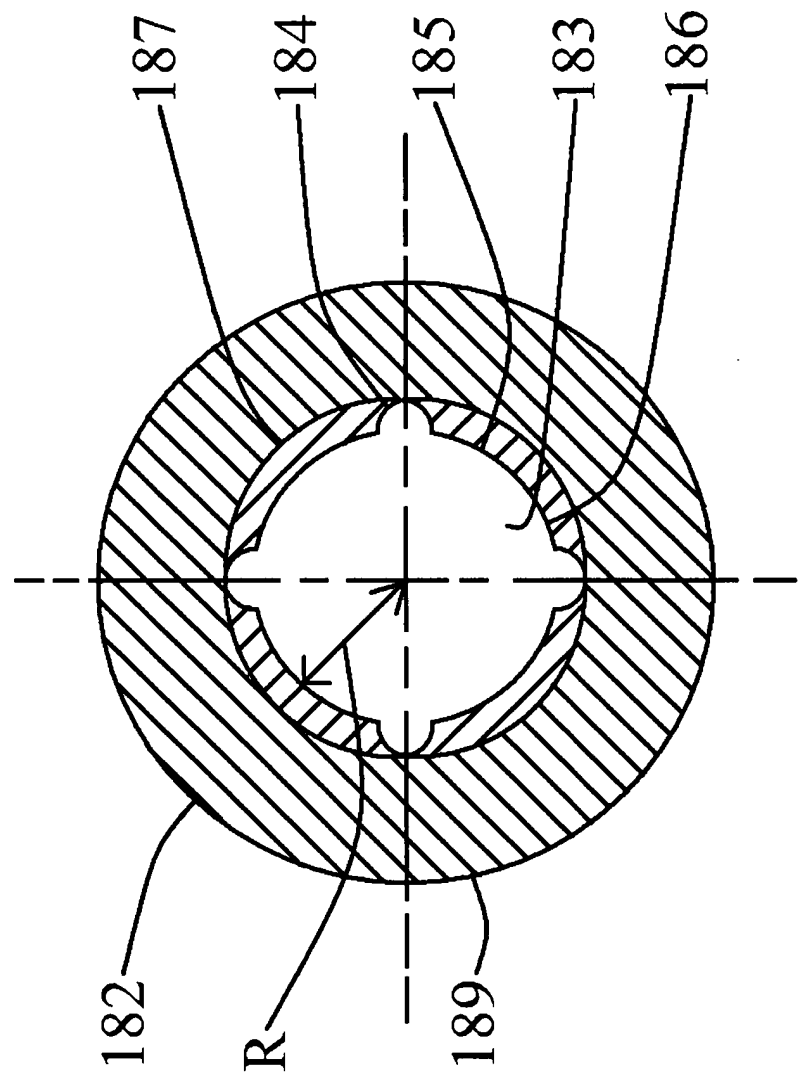


Figure 5a

200 →

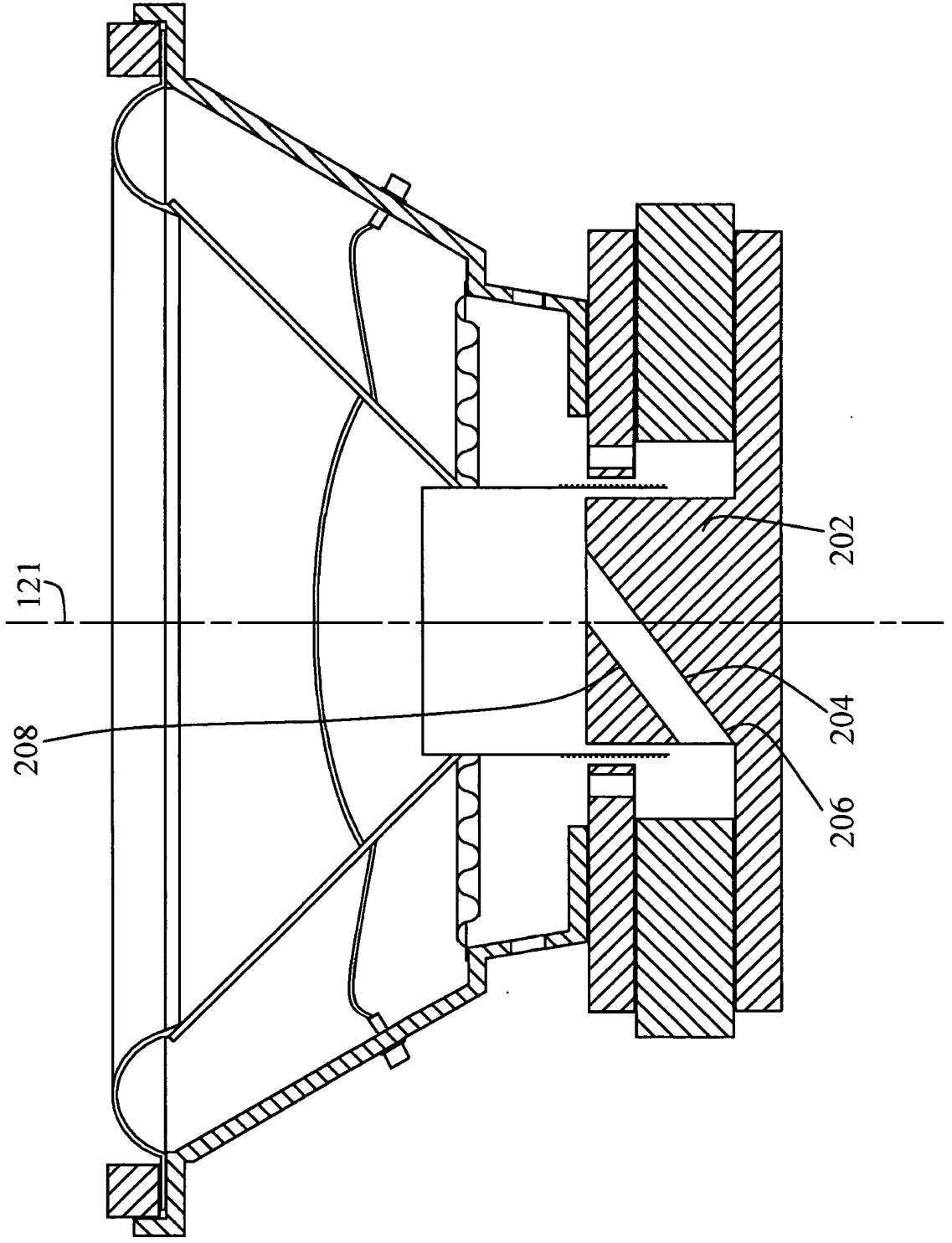


Figure 5b

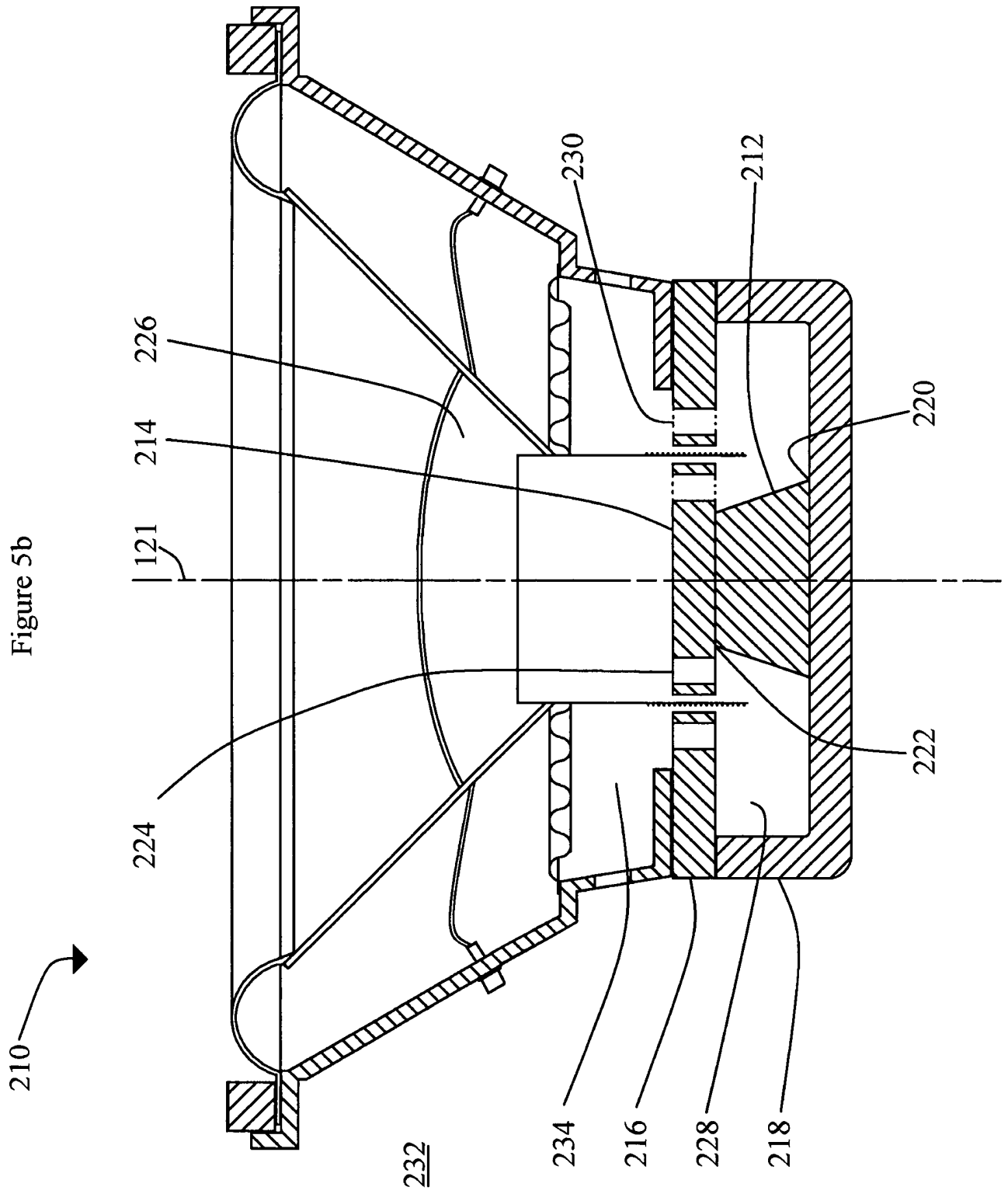




Figure 6a

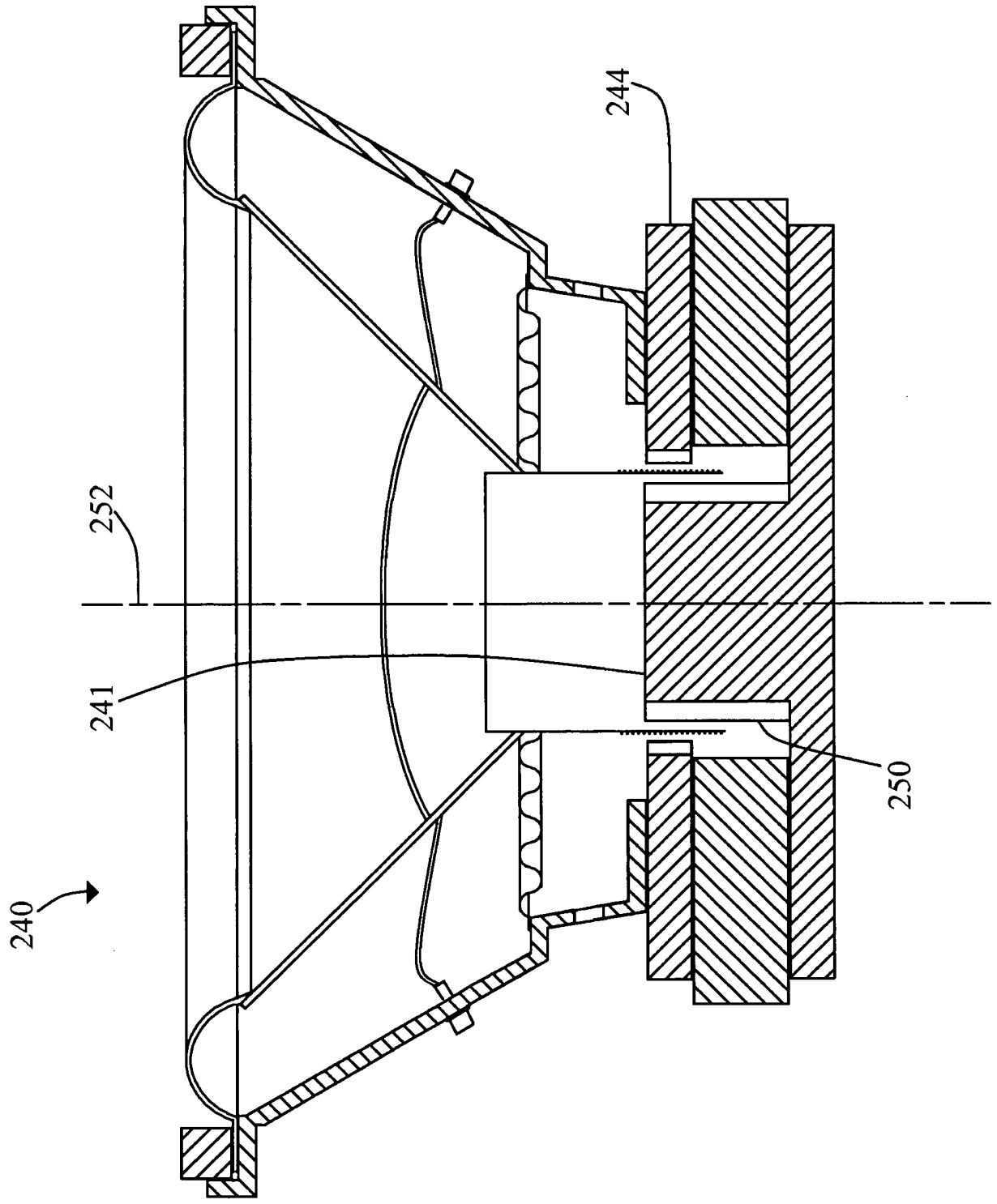


Figure 6b

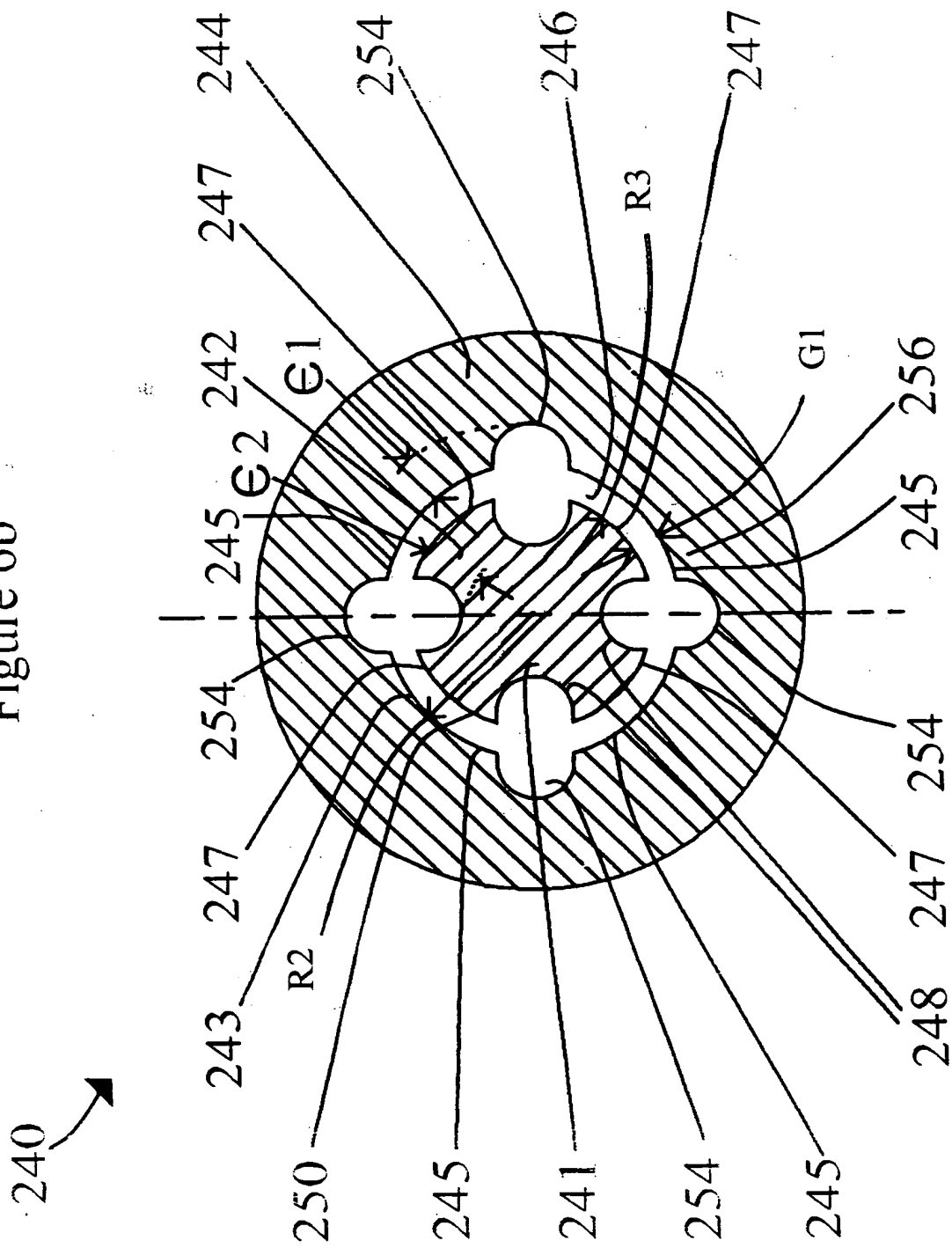


Figure 7

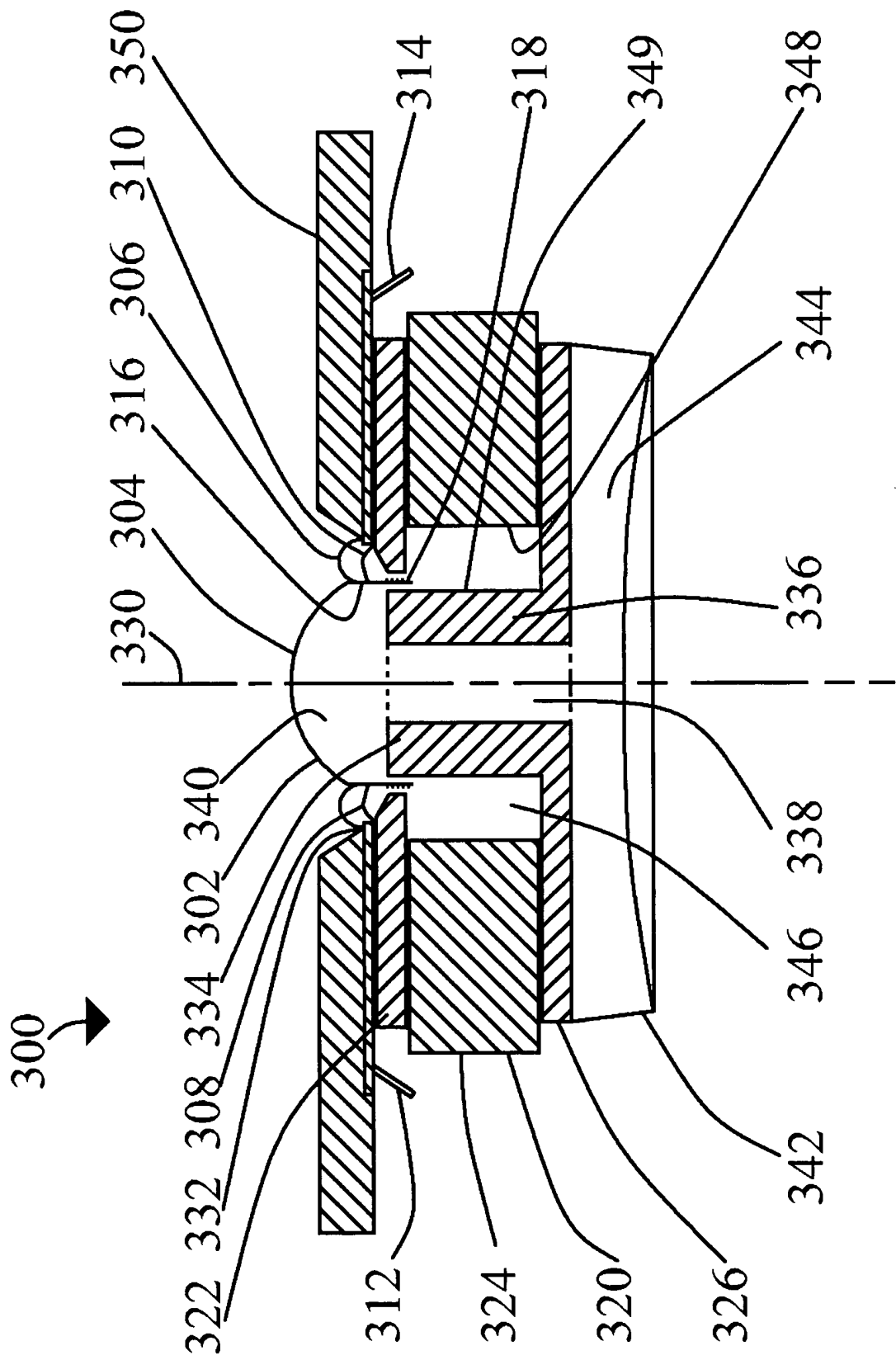
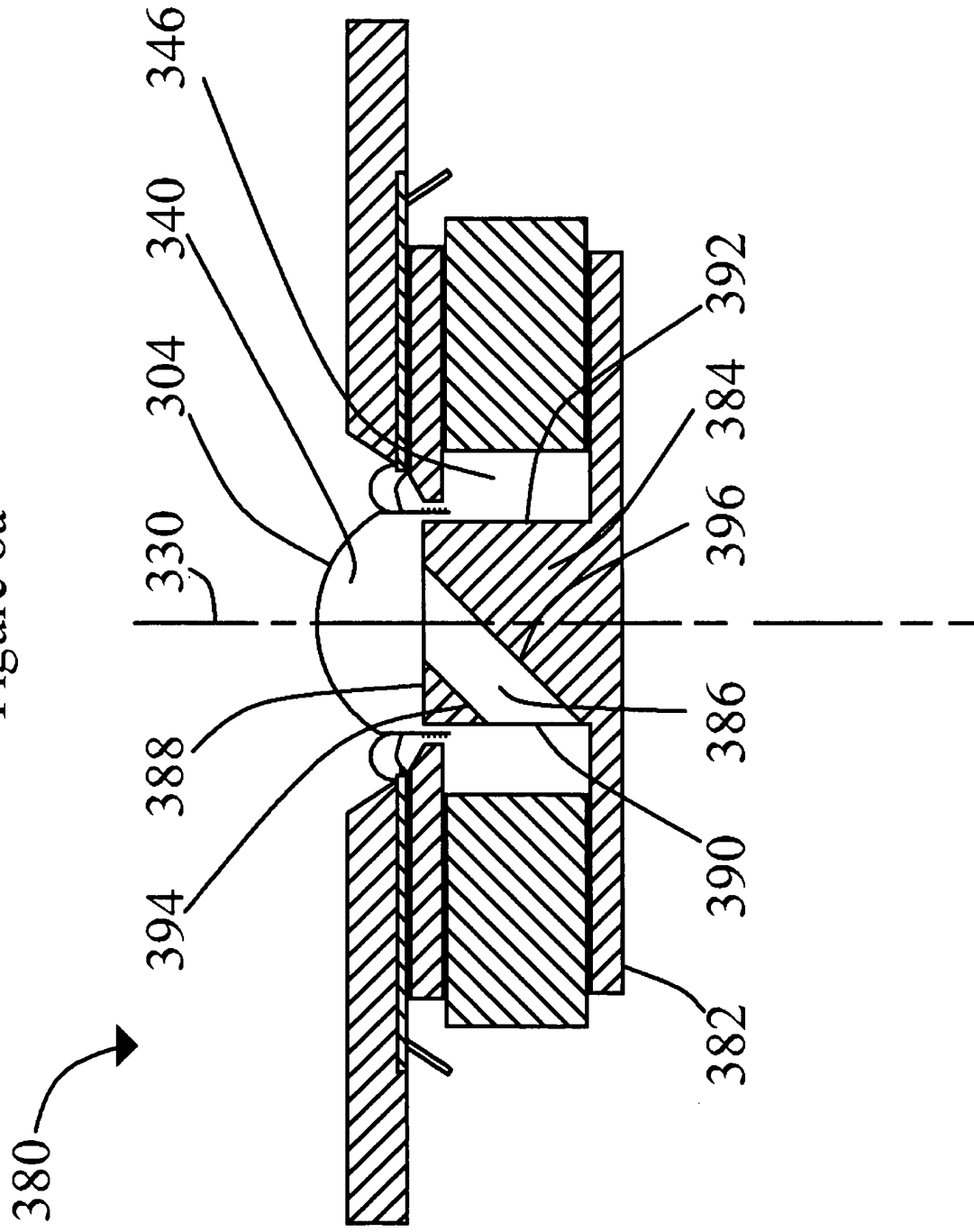


Figure 8a



A cross-sectional view of a semiconductor device 400. The device features a central channel 404 flanked by gate structures 412 and 416. Source/drain regions 402 and 408 are located on either side of the channel. The entire structure is built on a substrate 418. The gate structures 412 and 416 are shown with a hatched pattern, indicating a different material or layer. The channel 404 is a central opening. The source/drain regions 402 and 408 are also shown with a hatched pattern. The substrate 418 is the bottom layer of the device.

